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International Bureau

INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification 6 : H01L 21/302 — A1

(11) International Publication Number: WO 98/50948

(43) International Publication Date: 12 November 1998 (12.11.98)

(21) International Application Number: PCT/US98/08936

(22) International Filing Date: 1 May 1998 (01.05.98)

(30) Priority Data:
9/114556 — 2 May 1997 (02.05.97) — JP
09/070,680 — 30 April 1998 (30.04.98) — US

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(81) Designated States: CN, JP, KR, SG, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).

Published
With international search report.

9905161-7
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(54) Title: METHOD FOR ETCHING SILICON WAFER

(57) Abstract

A method for etching a silicon wafer includes the steps of: lapping a silicon wafer; etching the silicon wafer; and polishing the silicon wafer; wherein the etching step includes an etching treatment and a rinsing treatment, and at least an oxidizing agent is added to a rinse to be used for the rinsing treatment, thereby forming an oxidation film on a surface of the silicon wafer.